

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-GSM850-128CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 66.95 V/m; Power Drift = -0.04 dB

PMF = 2.830 is applied.

E-field emissions = 153.2 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

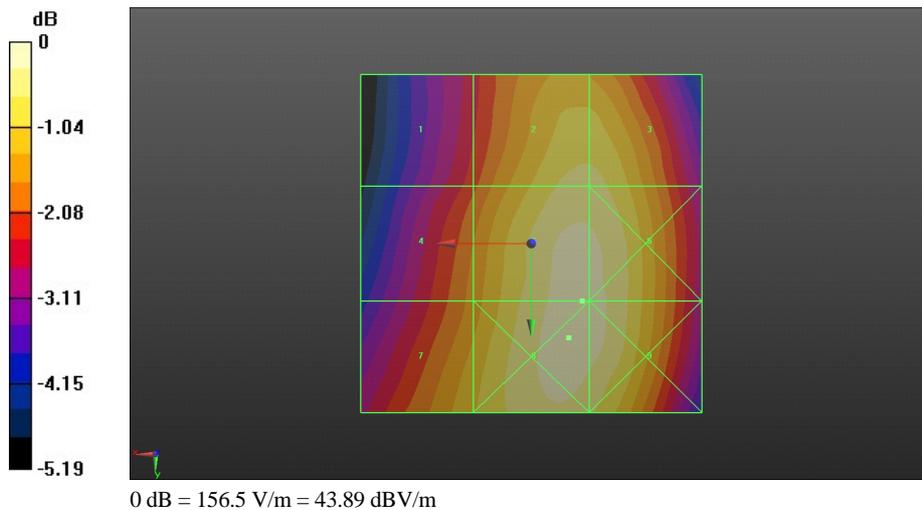
Grid 1 M4 122.0 V/m	Grid 2 M4 146.9 V/m	Grid 3 M4 146.9 V/m
Grid 4 M4 130.7 V/m	Grid 5 M3 153.2 V/m	Grid 6 M3 152.9 V/m
Grid 7 M4 138.3 V/m	Grid 8 M3 153.7 V/m	Grid 9 M3 153.1 V/m

Cursor:

Total = 153.7 V/m

E Category: M3

Location: -5.5, 14, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-GSM850-190CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 72.50 V/m; Power Drift = -0.03 dB

PMF = 2.830 is applied.

E-field emissions = 166.4 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

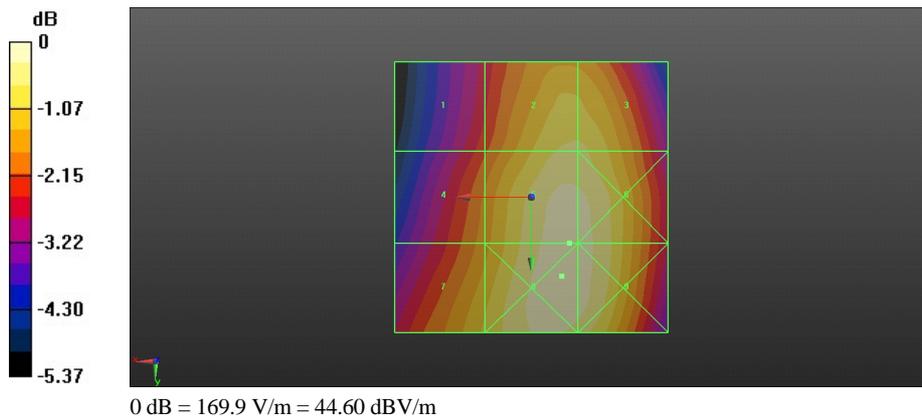
Grid 1 M4 131.6 V/m	Grid 2 M3 158.0 V/m	Grid 3 M3 157.9 V/m
Grid 4 M4 142.0 V/m	Grid 5 M3 166.4 V/m	Grid 6 M3 166.1 V/m
Grid 7 M3 151.3 V/m	Grid 8 M3 166.9 V/m	Grid 9 M3 166.3 V/m

Cursor:

Total = 166.9 V/m

E Category: M3

Location: -5.5, 14.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-GSM850-251CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 73.90 V/m; Power Drift = 0.04 dB

PMF = 2.830 is applied.

E-field emissions = 169.9 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

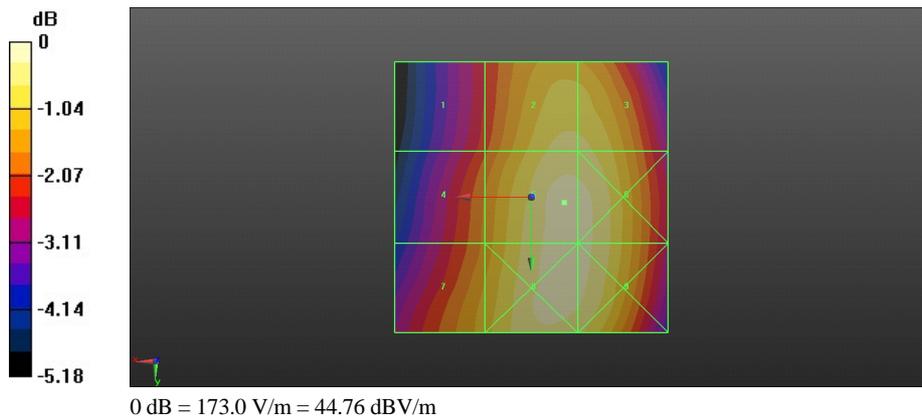
Grid 1 M4 135.2 V/m	Grid 2 M3 162.7 V/m	Grid 3 M3 162.3 V/m
Grid 4 M4 143.8 V/m	Grid 5 M3 169.9 V/m	Grid 6 M3 169.2 V/m
Grid 7 M3 151.2 V/m	Grid 8 M3 169.9 V/m	Grid 9 M3 169.2 V/m

Cursor:

Total = 169.9 V/m

E Category: M3

Location: -6, 1, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-GSM850-128CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06200 A/m; Power Drift = 0.14 dB

PMF = 2.820 is applied.

H-field emissions = 0.2380 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

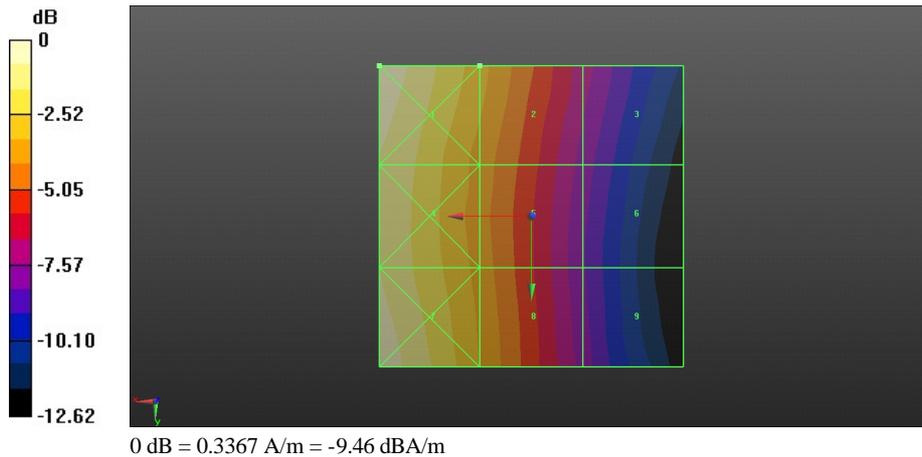
Grid 1 M4 0.330 A/m	Grid 2 M4 0.238 A/m	Grid 3 M4 0.149 A/m
Grid 4 M4 0.306 A/m	Grid 5 M4 0.220 A/m	Grid 6 M4 0.136 A/m
Grid 7 M4 0.328 A/m	Grid 8 M4 0.228 A/m	Grid 9 M4 0.136 A/m

Cursor:

Total = 0.3295 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-GSM850-190CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06600 A/m; Power Drift = 0.14 dB

PMF = 2.820 is applied.

H-field emissions = 0.2591 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

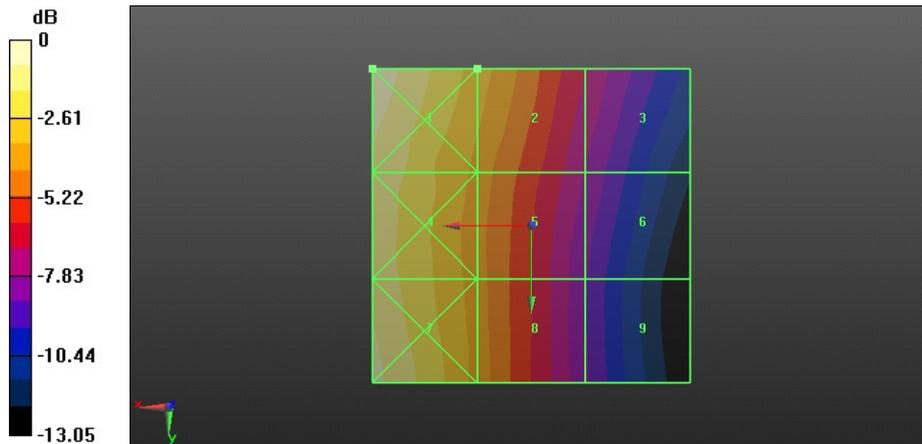
Grid 1 M4 0.359 A/m	Grid 2 M4 0.259 A/m	Grid 3 M4 0.165 A/m
Grid 4 M4 0.328 A/m	Grid 5 M4 0.238 A/m	Grid 6 M4 0.148 A/m
Grid 7 M4 0.343 A/m	Grid 8 M4 0.237 A/m	Grid 9 M4 0.138 A/m

Cursor:

Total = 0.3586 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.3663 A/m = -8.72 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-GSM850-251CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07200 A/m; Power Drift = -0.01 dB

PMF = 2.820 is applied.

H-field emissions = 0.2753 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

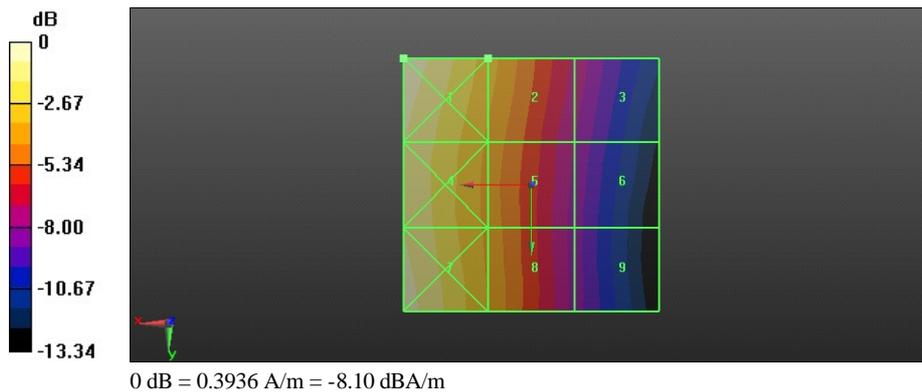
Grid 1 M4 0.385 A/m	Grid 2 M4 0.275 A/m	Grid 3 M4 0.170 A/m
Grid 4 M4 0.357 A/m	Grid 5 M4 0.257 A/m	Grid 6 M4 0.157 A/m
Grid 7 M4 0.374 A/m	Grid 8 M4 0.261 A/m	Grid 9 M4 0.151 A/m

Cursor:

Total = 0.3853 A/m

H Category: M4

Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-GSM1900-512CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 24.17 V/m; Power Drift = 0.07 dB

PMF = 2.860 is applied.

E-field emissions = 79.88 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

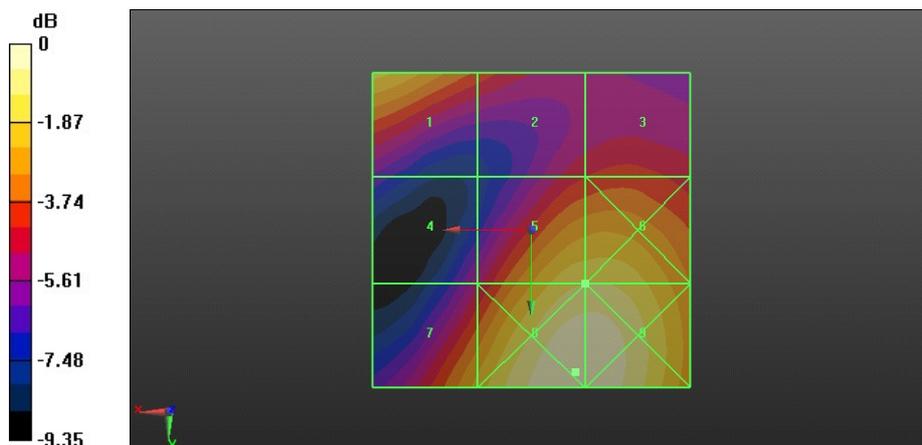
Grid 1 M3	Grid 2 M3	Grid 3 M3
76.93 V/m	59.33 V/m	57.80 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
50.72 V/m	79.88 V/m	80.22 V/m
Grid 7 M3	Grid 8 M2	Grid 9 M2
71.28 V/m	91.49 V/m	91.31 V/m

Cursor:

Total = 91.49 V/m

E Category: M2

Location: -7, 22.5, 8.7 mm



0 dB = 92.16 V/m = 39.29 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-GSM1900-661CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 24.75 V/m; Power Drift = 0.09 dB

PMF = 2.860 is applied.

E-field emissions = 81.81 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

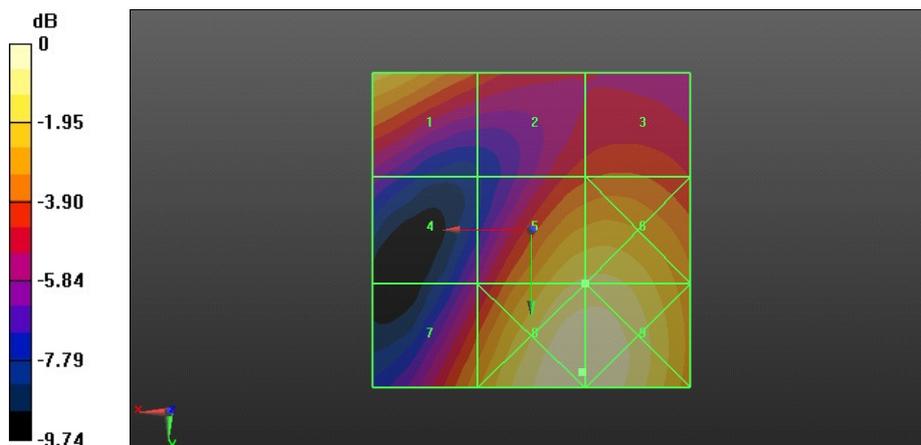
Grid 1 M3	Grid 2 M3	Grid 3 M3
77.61 V/m	59.59 V/m	60.29 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
48.60 V/m	81.81 V/m	82.28 V/m
Grid 7 M3	Grid 8 M2	Grid 9 M2
68.18 V/m	92.46 V/m	92.44 V/m

Cursor:

Total = 92.46 V/m

E Category: M2

Location: -8, 22.5, 8.7 mm



0 dB = 93.14 V/m = 39.38 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-GSM1900-810CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 25.34 V/m; Power Drift = -0.00 dB

PMF = 2.860 is applied.

E-field emissions = 82.37 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

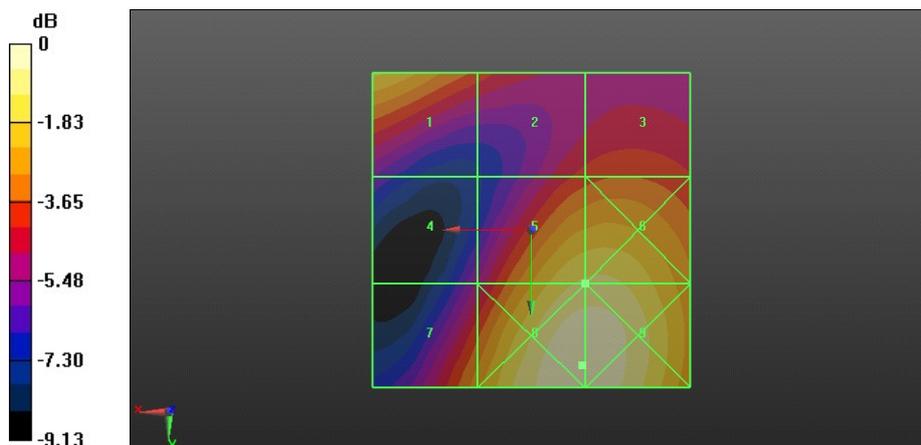
Grid 1 M3	Grid 2 M3	Grid 3 M3
77.15 V/m	60.38 V/m	61.34 V/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
50.38 V/m	82.37 V/m	82.84 V/m
Grid 7 M3	Grid 8 M2	Grid 9 M2
68.68 V/m	92.60 V/m	92.58 V/m

Cursor:

Total = 92.60 V/m

E Category: M2

Location: -8, 21.5, 8.7 mm



0 dB = 93.29 V/m = 39.40 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-GSM1900-512CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07900 A/m; Power Drift = -0.03 dB

PMF = 2.830 is applied.

H-field emissions = 0.2180 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

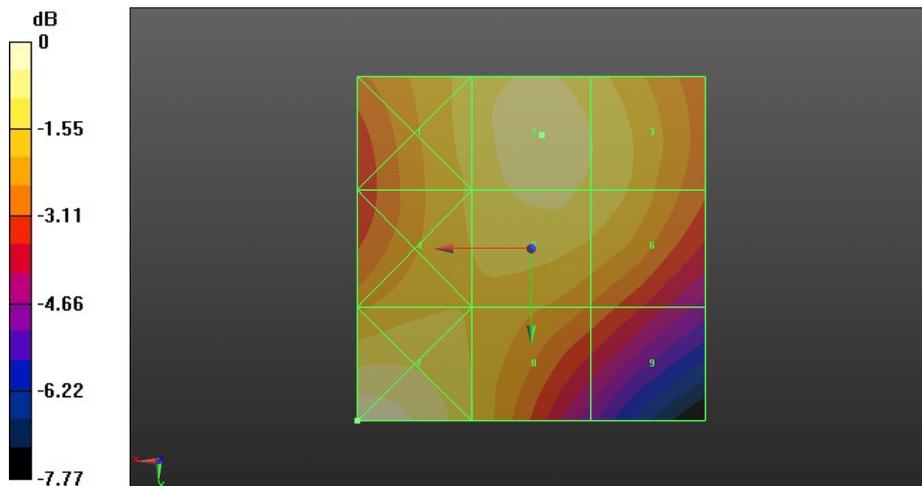
Grid 1 M3 0.205 A/m	Grid 2 M3 0.218 A/m	Grid 3 M3 0.212 A/m
Grid 4 M3 0.202 A/m	Grid 5 M3 0.214 A/m	Grid 6 M3 0.209 A/m
Grid 7 M3 0.234 A/m	Grid 8 M3 0.200 A/m	Grid 9 M3 0.176 A/m

Cursor:

Total = 0.2336 A/m

H Category: M3

Location: 25, 25, 8.7 mm



0 dB = 0.2379 A/m = -12.47 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-GSM1900-661CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08200 A/m; Power Drift = 0.07 dB

PMF = 2.830 is applied.

H-field emissions = 0.2265 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

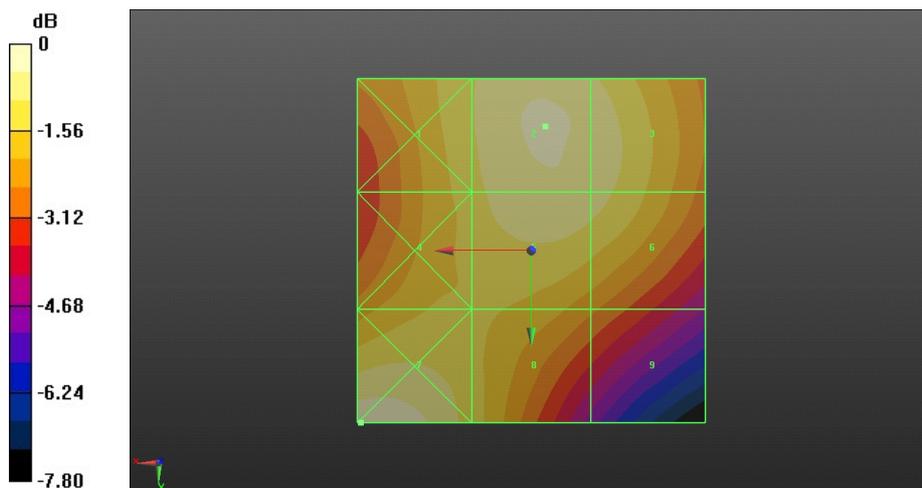
Grid 1 M3 0.211 A/m	Grid 2 M3 0.226 A/m	Grid 3 M3 0.221 A/m
Grid 4 M3 0.207 A/m	Grid 5 M3 0.222 A/m	Grid 6 M3 0.218 A/m
Grid 7 M3 0.234 A/m	Grid 8 M3 0.205 A/m	Grid 9 M3 0.180 A/m

Cursor:

Total = 0.2343 A/m

H Category: M3

Location: 24.5, 25, 8.7 mm



0 dB = 0.2385 A/m = -12.45 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-GSM1900-810CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08200 A/m; Power Drift = -0.00 dB

PMF = 2.830 is applied.

H-field emissions = 0.2278 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

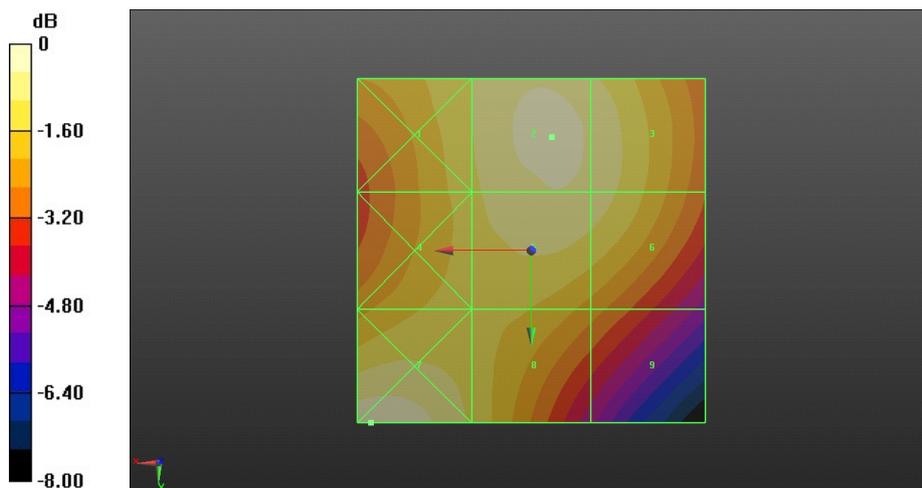
Grid 1 M3 0.210 A/m	Grid 2 M3 0.228 A/m	Grid 3 M3 0.221 A/m
Grid 4 M3 0.207 A/m	Grid 5 M3 0.223 A/m	Grid 6 M3 0.218 A/m
Grid 7 M3 0.233 A/m	Grid 8 M3 0.208 A/m	Grid 9 M3 0.181 A/m

Cursor:

Total = 0.2333 A/m

H Category: M3

Location: 23, 25, 8.7 mm



0 dB = 0.2375 A/m = -12.49 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band V-4132CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 64.80 V/m; Power Drift = -0.05 dB

PMF = 1.040 is applied.

E-field emissions = 54.30 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

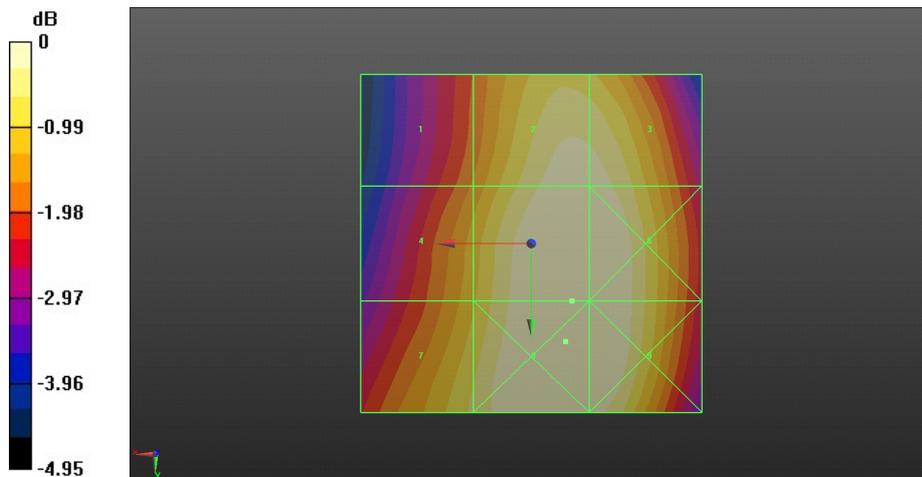
Grid 1 M4 43.79 V/m	Grid 2 M4 52.19 V/m	Grid 3 M4 51.95 V/m
Grid 4 M4 46.62 V/m	Grid 5 M4 54.30 V/m	Grid 6 M4 54.01 V/m
Grid 7 M4 49.11 V/m	Grid 8 M4 54.58 V/m	Grid 9 M4 54.07 V/m

Cursor:

Total = 54.58 V/m

E Category: M4

Location: -5, 14.5, 8.7 mm



0 dB = 52.48 V/m = 34.40 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band V-4182CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 67.15 V/m; Power Drift = 0.06 dB

PMF = 1.040 is applied.

E-field emissions = 57.22 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

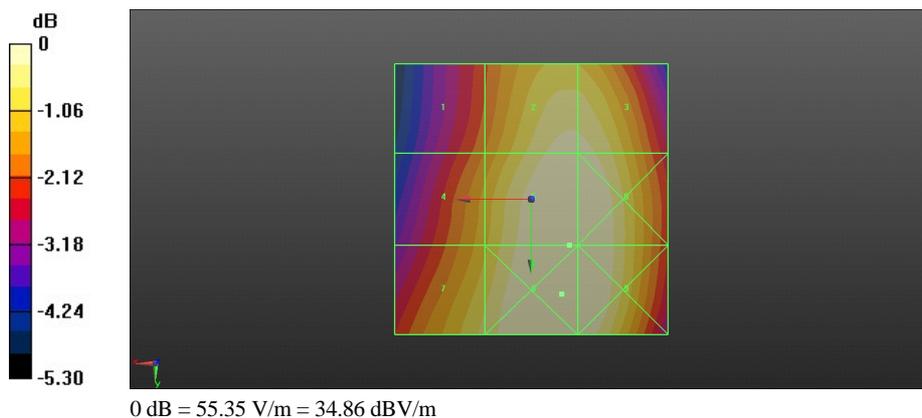
Grid 1 M4 45.29 V/m	Grid 2 M4 54.34 V/m	Grid 3 M4 54.27 V/m
Grid 4 M4 48.62 V/m	Grid 5 M4 57.22 V/m	Grid 6 M4 57.06 V/m
Grid 7 M4 51.79 V/m	Grid 8 M4 57.57 V/m	Grid 9 M4 57.29 V/m

Cursor:

Total = 57.57 V/m

E Category: M4

Location: -5.5, 17.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band V-4233CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 70.36 V/m; Power Drift = 0.01 dB

PMF = 1.040 is applied.

E-field emissions = 59.61 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

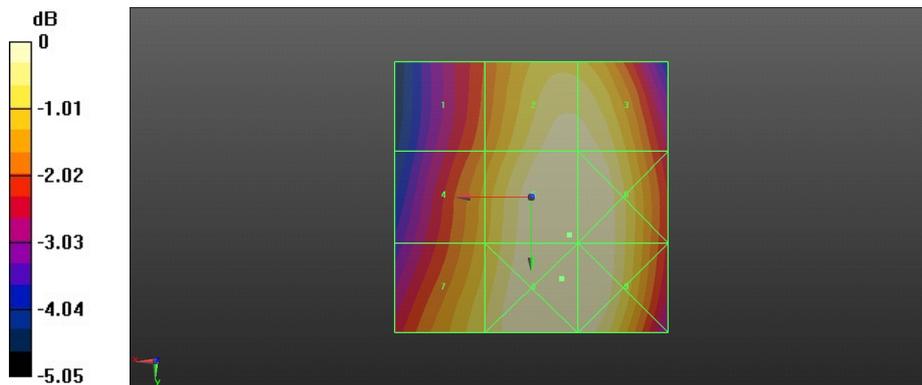
Grid 1 M4 47.78 V/m	Grid 2 M4 57.17 V/m	Grid 3 M4 57.04 V/m
Grid 4 M4 50.80 V/m	Grid 5 M4 59.61 V/m	Grid 6 M4 59.52 V/m
Grid 7 M4 53.52 V/m	Grid 8 M4 59.89 V/m	Grid 9 M4 59.59 V/m

Cursor:

Total = 59.89 V/m

E Category: M4

Location: -5.5, 15, 8.7 mm



0 dB = 57.58 V/m = 35.21 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band V-4132CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06000 A/m; Power Drift = 0.02 dB

PMF = 1.020 is applied.

H-field emissions = 0.08265 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

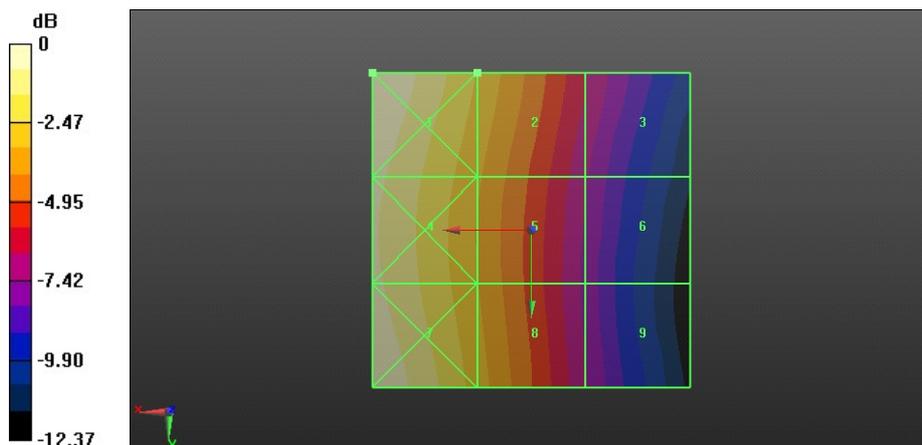
Grid 1 M4 0.113 A/m	Grid 2 M4 0.083 A/m	Grid 3 M4 0.052 A/m
Grid 4 M4 0.104 A/m	Grid 5 M4 0.077 A/m	Grid 6 M4 0.048 A/m
Grid 7 M4 0.111 A/m	Grid 8 M4 0.079 A/m	Grid 9 M4 0.048 A/m

Cursor:

Total = 0.1125 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1103 A/m = -19.15 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band V-4182CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06100 A/m; Power Drift = -0.01 dB

PMF = 1.020 is applied.

H-field emissions = 0.08511 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

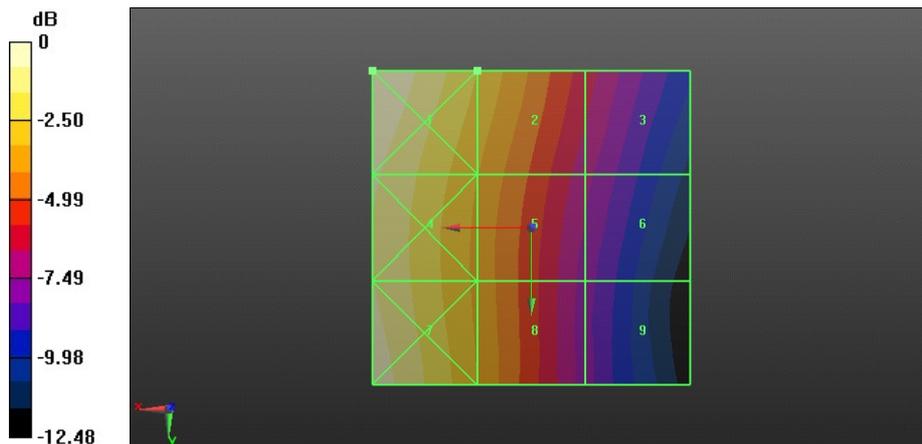
Grid 1 M4 0.116 A/m	Grid 2 M4 0.085 A/m	Grid 3 M4 0.055 A/m
Grid 4 M4 0.105 A/m	Grid 5 M4 0.078 A/m	Grid 6 M4 0.050 A/m
Grid 7 M4 0.109 A/m	Grid 8 M4 0.077 A/m	Grid 9 M4 0.046 A/m

Cursor:

Total = 0.1156 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1133 A/m = -18.92 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band V-4233CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

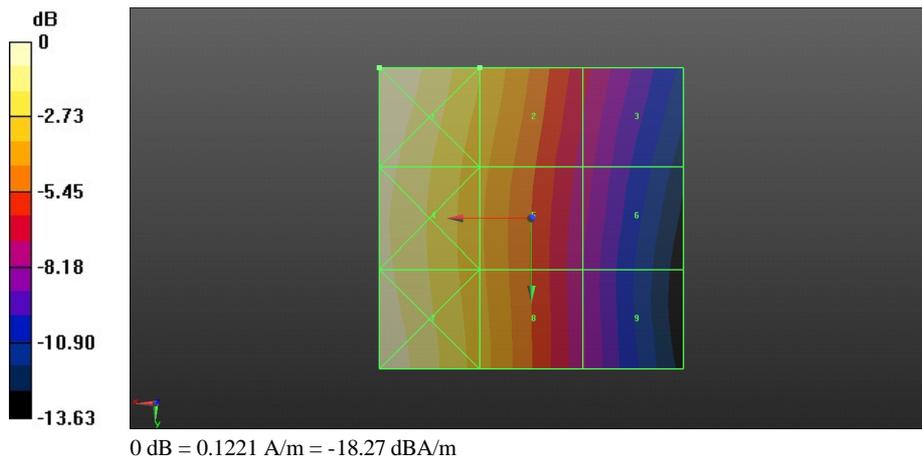
Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.06500 A/m; Power Drift = 0.02 dB
 PMF = 1.020 is applied.
 H-field emissions = 0.08987 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.125 A/m	Grid 2 M4 0.090 A/m	Grid 3 M4 0.055 A/m
Grid 4 M4 0.115 A/m	Grid 5 M4 0.083 A/m	Grid 6 M4 0.051 A/m
Grid 7 M4 0.120 A/m	Grid 8 M4 0.085 A/m	Grid 9 M4 0.049 A/m

Cursor:

Total = 0.1246 A/m
 H Category: M4
 Location: 25, -25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band IV-1312CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 33.90 V/m; Power Drift = 0.10 dB

PMF = 1.020 is applied.

E-field emissions = 40.49 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

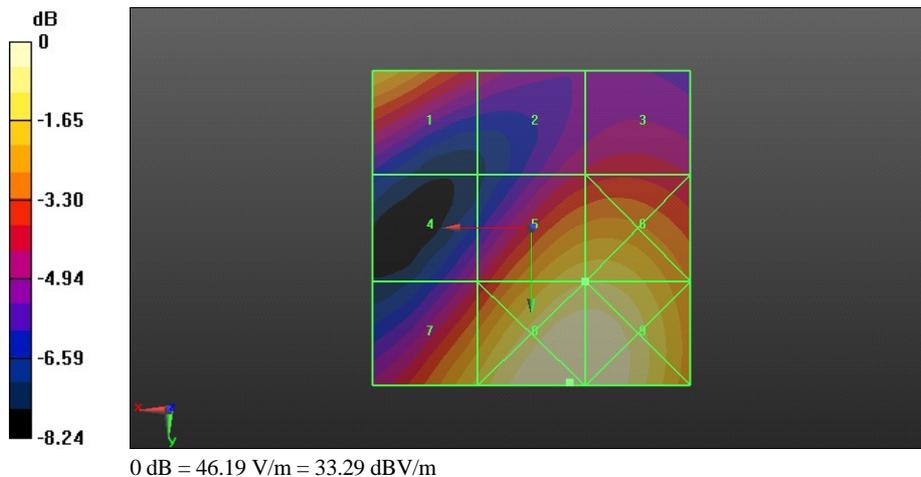
Grid 1 M4 38.66 V/m	Grid 2 M4 28.51 V/m	Grid 3 M4 29.43 V/m
Grid 4 M4 27.84 V/m	Grid 5 M4 40.49 V/m	Grid 6 M4 40.63 V/m
Grid 7 M4 39.08 V/m	Grid 8 M4 47.12 V/m	Grid 9 M4 46.87 V/m

Cursor:

Total = 47.12 V/m

E Category: M4

Location: -6, 24.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band IV-1413CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 35.11 V/m; Power Drift = 0.05 dB

PMF = 1.020 is applied.

E-field emissions = 41.15 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

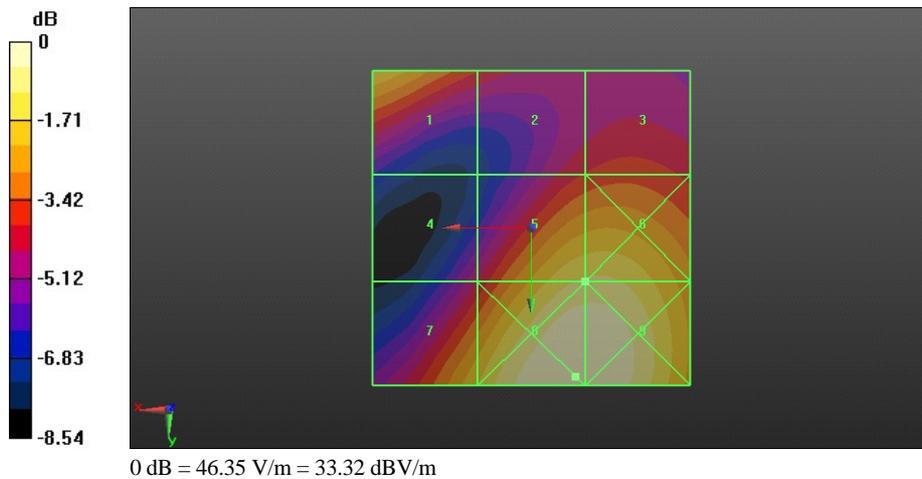
Grid 1 M4 38.46 V/m	Grid 2 M4 29.59 V/m	Grid 3 M4 30.56 V/m
Grid 4 M4 27.57 V/m	Grid 5 M4 41.15 V/m	Grid 6 M4 41.33 V/m
Grid 7 M4 38.13 V/m	Grid 8 M4 47.28 V/m	Grid 9 M4 47.16 V/m

Cursor:

Total = 47.28 V/m

E Category: M4

Location: -7, 23.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band IV-1513CH**DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 36.54 V/m; Power Drift = -0.18 dB

PMF = 1.020 is applied.

E-field emissions = 41.09 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

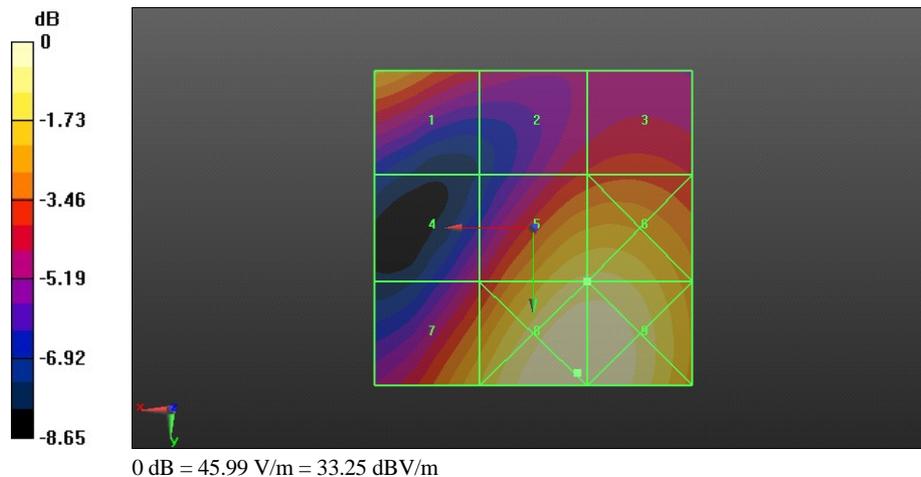
Grid 1 M4 36.12 V/m	Grid 2 M4 29.37 V/m	Grid 3 M4 30.47 V/m
Grid 4 M4 27.55 V/m	Grid 5 M4 41.09 V/m	Grid 6 M4 41.26 V/m
Grid 7 M4 37.80 V/m	Grid 8 M4 46.91 V/m	Grid 9 M4 46.80 V/m

Cursor:

Total = 46.91 V/m

E Category: M4

Location: -7, 23, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band IV-1312CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1120 A/m; Power Drift = 0.02 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1095 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

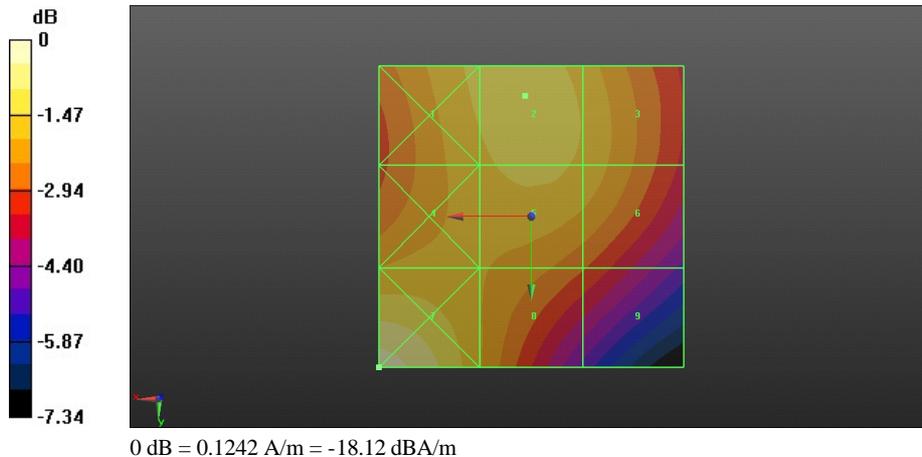
Grid 1 M4 0.107 A/m	Grid 2 M4 0.109 A/m	Grid 3 M4 0.105 A/m
Grid 4 M4 0.103 A/m	Grid 5 M4 0.107 A/m	Grid 6 M4 0.103 A/m
Grid 7 M4 0.122 A/m	Grid 8 M4 0.100 A/m	Grid 9 M4 0.089 A/m

Cursor:

Total = 0.1217 A/m

H Category: M4

Location: 25, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band IV-1413CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1220 A/m; Power Drift = -0.01 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1146 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

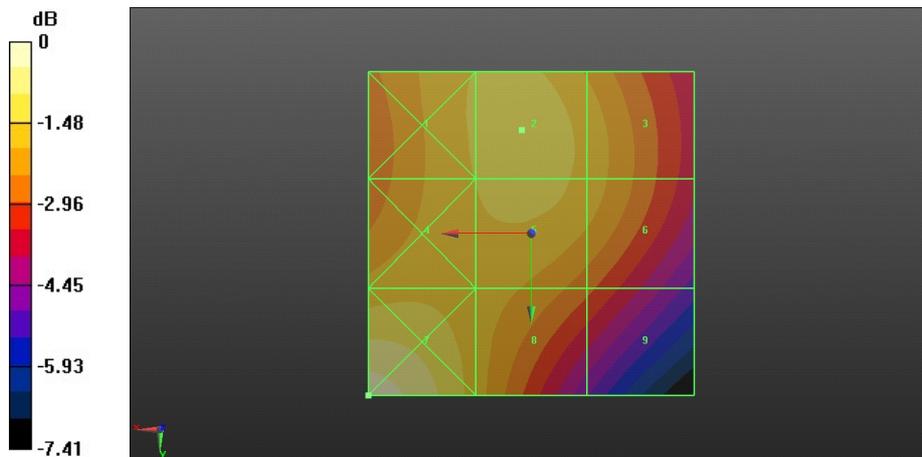
Grid 1 M4 0.112 A/m	Grid 2 M4 0.115 A/m	Grid 3 M4 0.109 A/m
Grid 4 M4 0.111 A/m	Grid 5 M4 0.113 A/m	Grid 6 M4 0.108 A/m
Grid 7 M4 0.129 A/m	Grid 8 M4 0.108 A/m	Grid 9 M4 0.095 A/m

Cursor:

Total = 0.1287 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1313 A/m = -17.63 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band IV-1513CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1210 A/m; Power Drift = -0.00 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1166 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

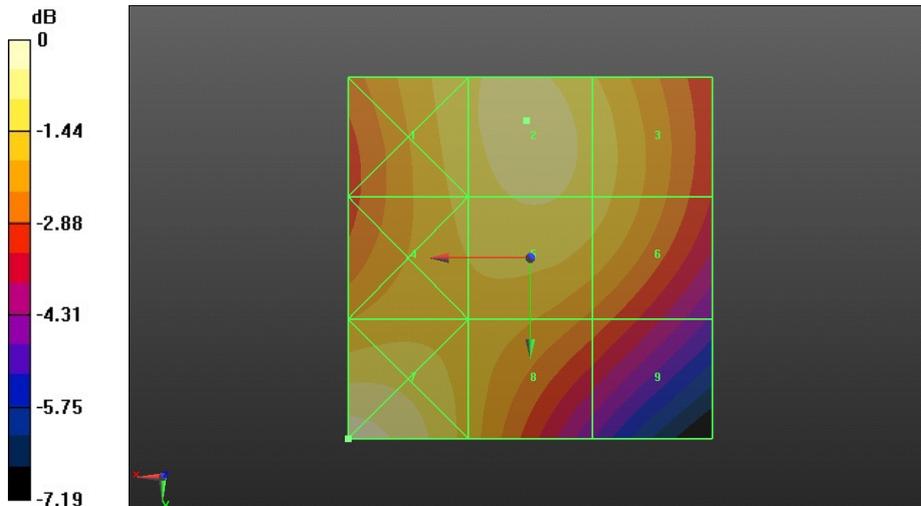
Grid 1 M4 0.112 A/m	Grid 2 M4 0.117 A/m	Grid 3 M4 0.112 A/m
Grid 4 M4 0.110 A/m	Grid 5 M4 0.114 A/m	Grid 6 M4 0.110 A/m
Grid 7 M4 0.124 A/m	Grid 8 M4 0.106 A/m	Grid 9 M4 0.095 A/m

Cursor:

Total = 0.1241 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1267 A/m = -17.94 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band II-9262CH**DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI**

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 36.57 V/m; Power Drift = -0.01 dB

PMF = 1.020 is applied.

E-field emissions = 42.22 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

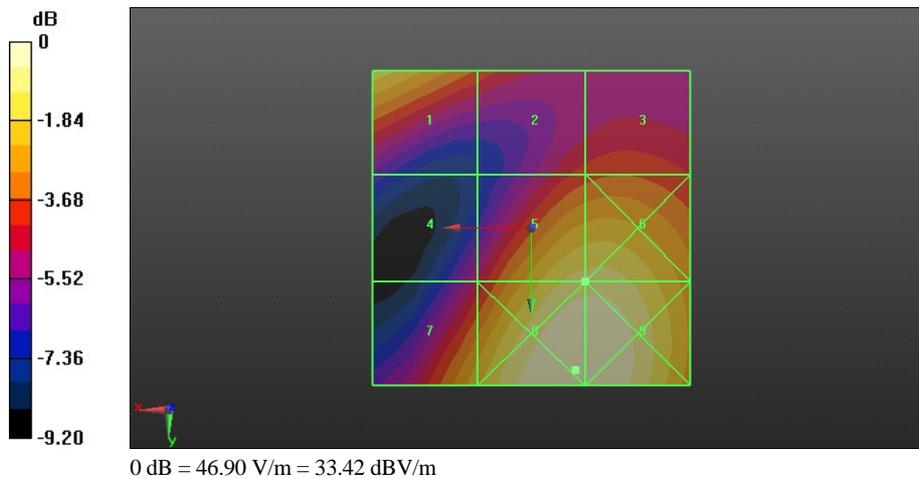
Grid 1 M4 39.95 V/m	Grid 2 M4 30.66 V/m	Grid 3 M4 30.66 V/m
Grid 4 M4 26.96 V/m	Grid 5 M4 42.22 V/m	Grid 6 M4 42.37 V/m
Grid 7 M4 37.26 V/m	Grid 8 M4 47.84 V/m	Grid 9 M4 47.74 V/m

Cursor:

Total = 47.84 V/m

E Category: M4

Location: -7, 22.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band II-9400CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 36.94 V/m; Power Drift = 0.14 dB

PMF = 1.020 is applied.

E-field emissions = 44.33 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

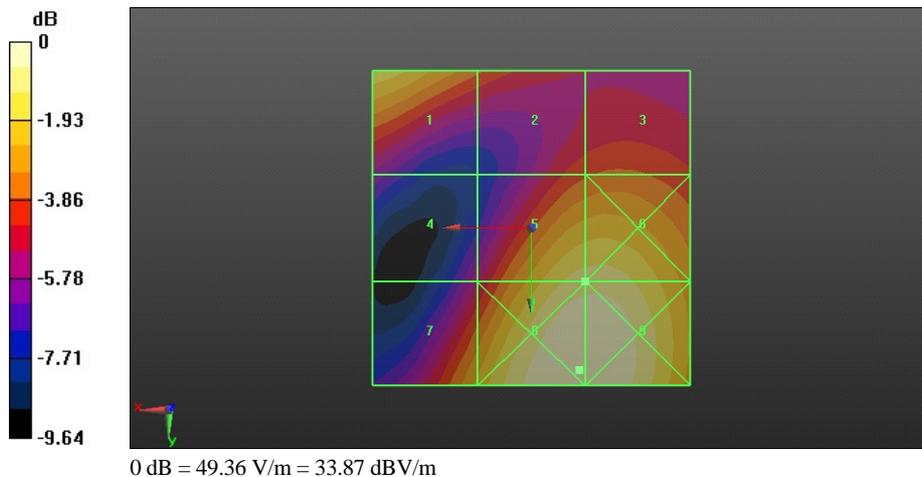
Grid 1 M4 42.02 V/m	Grid 2 M4 32.43 V/m	Grid 3 M4 32.22 V/m
Grid 4 M4 26.71 V/m	Grid 5 M4 44.33 V/m	Grid 6 M4 44.56 V/m
Grid 7 M4 37.48 V/m	Grid 8 M4 50.35 V/m	Grid 9 M4 50.31 V/m

Cursor:

Total = 50.35 V/m

E Category: M4

Location: -7.5, 22.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_U9200-1-UMTS Band II-9538CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 38.36 V/m; Power Drift = 0.05 dB

PMF = 1.020 is applied.

E-field emissions = 44.58 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

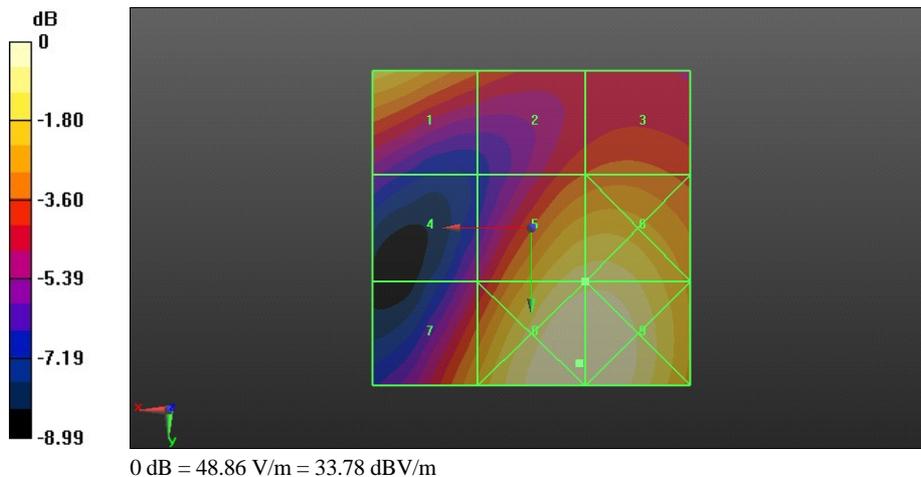
Grid 1 M4 41.52 V/m	Grid 2 M4 32.87 V/m	Grid 3 M4 33.51 V/m
Grid 4 M4 27.58 V/m	Grid 5 M4 44.58 V/m	Grid 6 M4 44.81 V/m
Grid 7 M4 37.53 V/m	Grid 8 M4 49.84 V/m	Grid 9 M4 49.81 V/m

Cursor:

Total = 49.84 V/m

E Category: M4

Location: -7.5, 21.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band II-9262CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

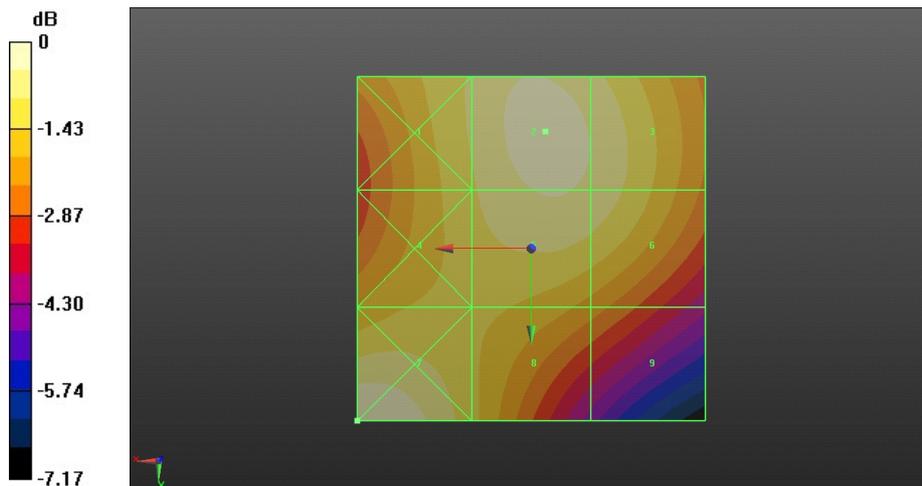
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.1120 A/m; Power Drift = -0.01 dB
 PMF = 1.010 is applied.
 H-field emissions = 0.1111 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.104 A/m	Grid 2 M4 0.111 A/m	Grid 3 M4 0.108 A/m
Grid 4 M4 0.102 A/m	Grid 5 M4 0.109 A/m	Grid 6 M4 0.107 A/m
Grid 7 M4 0.116 A/m	Grid 8 M4 0.099 A/m	Grid 9 M4 0.090 A/m

Cursor:
 Total = 0.1158 A/m
 H Category: M4
 Location: 25, 25, 8.7 mm



0 dB = 0.1146 A/m = -18.82 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band II-9400CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1210 A/m; Power Drift = -0.00 dB

PMF = 1.010 is applied.

H-field emissions = 0.1201 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

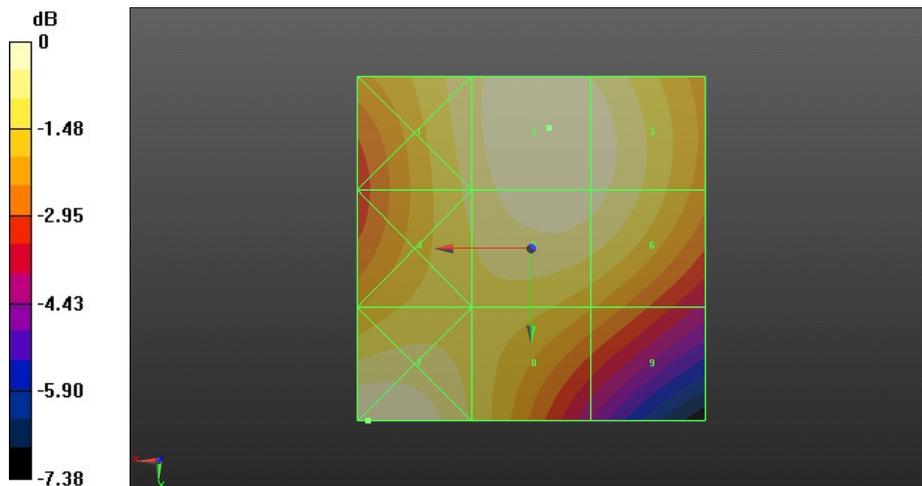
Grid 1 M4 0.112 A/m	Grid 2 M4 0.120 A/m	Grid 3 M4 0.118 A/m
Grid 4 M4 0.109 A/m	Grid 5 M4 0.118 A/m	Grid 6 M4 0.116 A/m
Grid 7 M4 0.121 A/m	Grid 8 M4 0.106 A/m	Grid 9 M4 0.096 A/m

Cursor:

Total = 0.1211 A/m

H Category: M4

Location: 23.5, 25, 8.7 mm



0 dB = 0.1199 A/m = -18.42 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_U9200-1-UMTS Band II-9538CH

DUT: U9200-1; Type: Ascend P1;HSPA+/HSUPA/HSDPA/UMTS/GSM/GPRS/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2011-11-16
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1200 A/m; Power Drift = -0.09 dB

PMF = 1.010 is applied.

H-field emissions = 0.1182 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

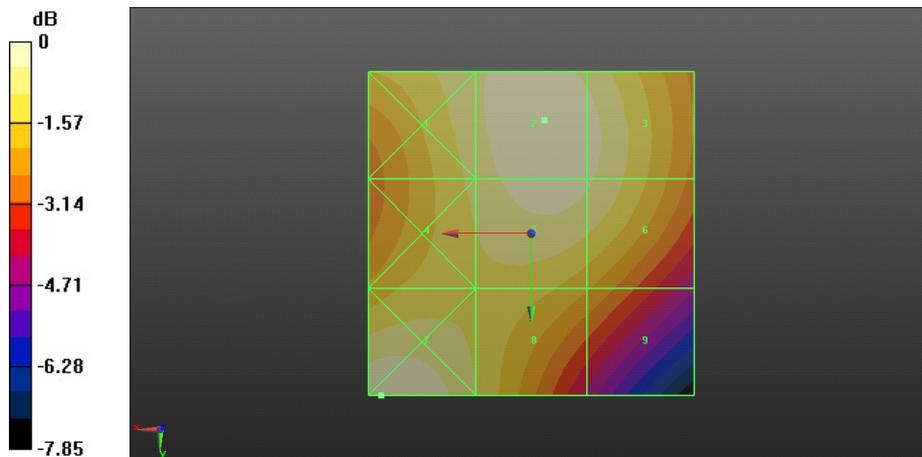
Grid 1 M4 0.111 A/m	Grid 2 M4 0.118 A/m	Grid 3 M4 0.115 A/m
Grid 4 M4 0.108 A/m	Grid 5 M4 0.116 A/m	Grid 6 M4 0.113 A/m
Grid 7 M4 0.120 A/m	Grid 8 M4 0.106 A/m	Grid 9 M4 0.094 A/m

Cursor:

Total = 0.1201 A/m

H Category: M4

Location: 23, 25, 8.7 mm



0 dB = 0.1189 A/m = -18.50 dBA/m